

substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch;

forming a photoresist film for a photolithographic process on said surface of said wafer; and

forming patterns on said surface of said wafer,

wherein an outer peripheral part of said wafer is chamfered in a thickness direction by mechanical chamfering, and

wherein said connecting portions are chamfered in a plane parallel to said main surface by mechanical chamfering.

15. A process for producing a semiconductor device according to claim 14, further comprising vapor-growing a film on the wafer surface.

16. A process for producing a semiconductor device according to claim 15, further comprising transporting said wafer.

17. A process for producing a semiconductor device according to claim 15, wherein said provided wafer is finished in a mirror wafer state.

18. A process for producing a semiconductor device according to claim 15, wherein said curved positioning notch does not divide the wafer into several sections.

19. A process for producing a semiconductor device according to claim 15, wherein said curved positioning notch does not cause loss of wafer structurable area for electronic components.

20. A process for producing a semiconductor device according to claim 14, wherein said curved positioning notch does not divide the wafer into several sections.

21. A process for producing a semiconductor device according to claim 14, wherein said curved positioning notch does not cause loss of wafer structurable area for electronic components.

22. A process for producing a semiconductor device according to claim 14, further comprising positioning said wafer by rotating said wafer.

23. A process for producing a semiconductor device according to claim 22, further comprising positioning said wafer by optical means.

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24. A process for producing a semiconductor device according to claim 14, further comprising transporting said wafer.

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25. A process for producing a semiconductor device according to claim 14, further comprising the step of diffusion.

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26. A process for producing a semiconductor device according to claim 14, further comprising the step of etching.

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27. A process for producing a semiconductor device according to claim 14, wherein said provided wafer is finished in a mirror wafer state.

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28. A process for producing a semiconductor device, comprising:
providing wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch;

forming a photoresist film for a photolithographic process on said surface of said wafer; and

forming patterns on said surface of said wafer,

wherein an outer peripheral part of said wafer is chamfered in a thickness direction by grindstone, and

wherein said connecting portions are chamfered in a plane parallel to said main surface by grindstone.

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15 16 29. A process for producing a semiconductor device according to claim 28, further comprising vapor-growing a film on the wafer surface.

16 17 30. A process for producing a semiconductor device according to claim 29, further comprising transporting said wafer.

16 18 31. A process for producing a semiconductor device according to claim 29, wherein said provided wafer is finished in a mirror wafer state.

16 19 32. A process for producing a semiconductor device according to claim 29, wherein said curved positioning notch does not divide the wafer into several sections.

19 20
33. A process for producing a semiconductor device according to claim 29, wherein said curved positioning notch does not cause loss of wafer structurable area for electronic components.

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34. A process for producing a semiconductor device according to claim 28, wherein said curved positioning notch does not divide the wafer into several sections.

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35. A process for producing a semiconductor device according to claim 28, wherein said curved positioning notch does not cause loss of wafer structurable area for electronic components.

23
36. A process for producing a semiconductor device according to claim 28, further comprising positioning said wafer by rotating said wafer.

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37. A process for producing a semiconductor device according to claim 36, further comprising positioning said wafer by optical means.

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38. A process for producing a semiconductor device according to claim 28, further comprising transporting said wafer.

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A process for producing a semiconductor device according to claim 28, further comprising the step of diffusion.

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A process for producing a semiconductor device according to claim 28, further comprising the step of etching.

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A process for producing a semiconductor device according to claim 28, wherein said provided wafer is finished in a mirror wafer state.

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A process for producing a semiconductor device comprising:

providing a wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch, wherein said connecting portions are chamfered in a plane parallel to said main surface;

forming a photoresist film for a photolithographic process on said surface of said wafer; and

forming patterns on said surface of said wafer,

wherein said curved positioning notch does not cause loss of wafer structurable area for electronic components.

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43. A process for producing a semiconductor device comprising:
providing a wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch, wherein said connecting portions are chamfered in a plane parallel to said main surface;
forming a photoresist film for a photolithographic process on said surface of said wafer; and
forming patterns on said surface of said wafer,
wherein said curved positioning notch does not divide the wafer into several sections.

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44. A process for producing a semiconductor device according to claim 43, wherein said curved positioning notch does not cause loss of wafer structurable area for electronic components.

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Respectfully submitted,

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